

YENG TAT ELECTRONICS

For RFID

CO., LTD.

Material characteristic

Material name		T4F	LF12	E2H	E9S	E9H	E5H	E6G	J2
Composition system		Ni-Zn	Ni-Zn	Ni-Zn	Ni-Zn	Ni-Zn	Ni-Zn	Ni-Zn	Mn-Zn
120-150KHz band		—	—	—	●	●	●	●	●
13.56MHz band		—	●	●	●	●	—	—	—
950MHz band		●	—	—	—	—	—	—	—
Initial permeability μ_i		8	120	130	240	250	900	1300	2800
Saturation magnetic flux density B_s	(mT)	210(4kA/m)	300(1.6kA/m)	400(1.6kA/m)	430(1.6kA/m)	430(1.6kA/m)	360(1.6kA/m)	330(1.6kA/m)	510(1.2kA/m)
Remanet flux density B_r	(mT)	130	130	250	310	300	210	180	140
Coercive force H_c	(A/m)	3040	200	136	56	48	28	20	12
Curie temperature T_c	(°C)	300 min.	250 min.	300 min.	260 min.	300 min.	150 min.	120 min.	200 min.
Volume resistivity ρ_v	($\Omega \cdot \text{cm}$)	10^6	10^7	10^7	10^6	10^7	10^7	10^7	300
Apparent specific density d	($\text{kg} \cdot \text{m}^{-3}$)	4.8×10^3	4.9×10^3	5.2×10^3	5.0×10^3	5.0×10^3	5.0×10^3	5.0×10^3	4.8×10^3

